Switching diode

DAN217U / BAV99U *1 / DAN217

*1 BAV99U is only sold in countries other than Japan.

●Application

Ultra high speed switching

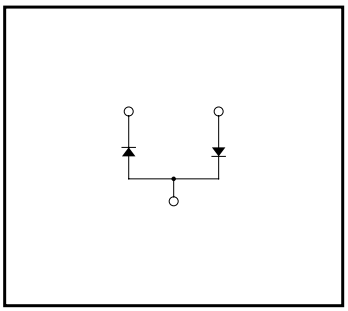
●Features

1) Small surface mounting type. (UMD3,SMD3)
2) Two diode elements are connected in series ($V_F \times 2$) per circuit.

●Construction

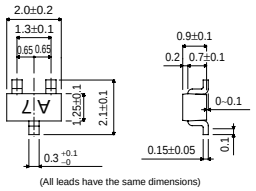
Silicon epitaxial planar

●Circuit



●External dimensions (Units : mm)

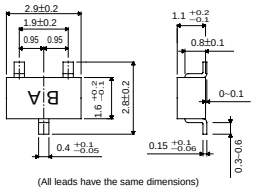
DAN217U / BAV99U



(All leads have the same dimensions)

ROHM : UMD3
EIAJ : SC–70
JEDEC : SOT–323

DAN217



(All leads have the same dimensions)

ROHM : SMD3
EIAJ : SC–59
JEDEC : SOT–346

●Absolute maximum ratings (Ta=25°C)

Type	Peak reverse voltage V_{RM}(V)	DC reverse voltage V_R(V)	Peak forward current I_{FM}(mA)	Mean rectifying current I_O(mA)	Surge current (1μs) I_{surge}(mA)	Power dissipation (TOTAL) Pd(mW)	Junction temperature Tj(°C)	Storage temperature Tstg(°C)
DAN217U	80	80	300	100	4000	200	150	–55 ~ +150
BAV99U	80	80	300	100	4000	200	150	–55 ~ +150
DAN217	80	80	300	100	4000	200	150	–55 ~ +150

●**Electrical characteristics** (Ta=25°C)

Type	Forward voltage		Reverse current		Fig
	V_F(V) Max.	Cond. I_F(mA)	I_R(μA) Max.	Cond. V_R(V)	
DAN217U	1.2	100	0.2	70	1 ~ 3
BAV99U	1.2	100	0.2	70	1 ~ 3
DAN217	1.2	100	0.1	70	4 ~ 6

●**Electrical characteristic curves** (Ta=25°C)

(DAN217U,BAV99U)···Fig.1~3

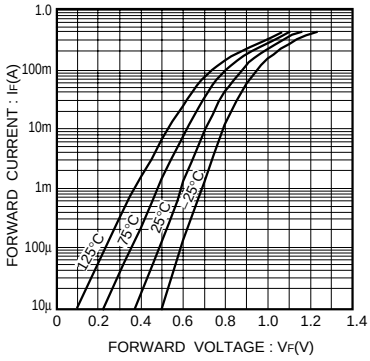


Fig.1 Forward characteristics

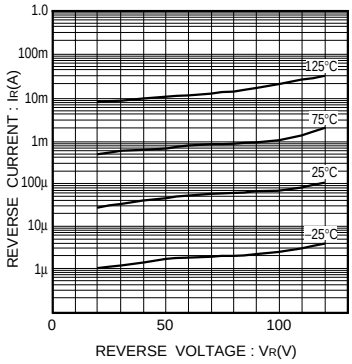


Fig.2 Reverse characteristics

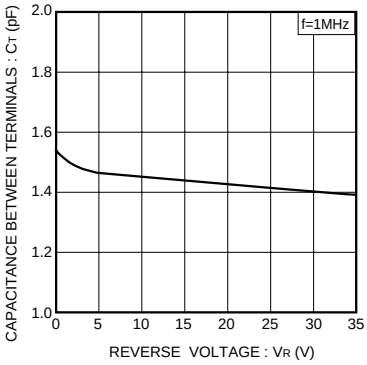


Fig.3 Capacitance between terminals characteristics

(DAN217) ···Fig.4~6

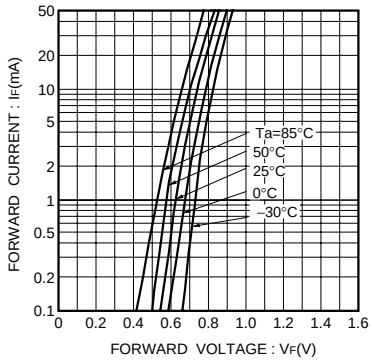


Fig.4 Forward characteristics

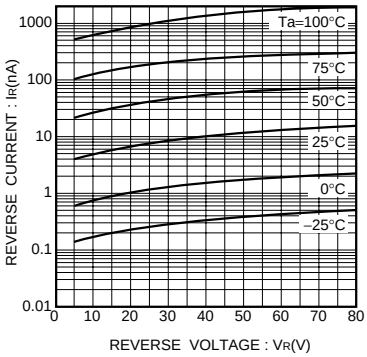


Fig.5 Reverse characteristics

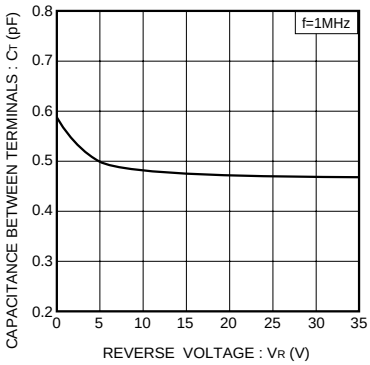


Fig.6 Capacitance between terminals characteristics